



STB13007DT4

High voltage fast-switching NPN power transistor

General features

- Improved specification: Lower leakage current, Tighter gain range, DC current gain preselection, Tighter storage time range
- High voltage capability
- Integrated free-wheeling diode
- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed
- Fully characterized at 125 °C
- Large RBSOA
- In compliance with the 2002/93/EC European Directive

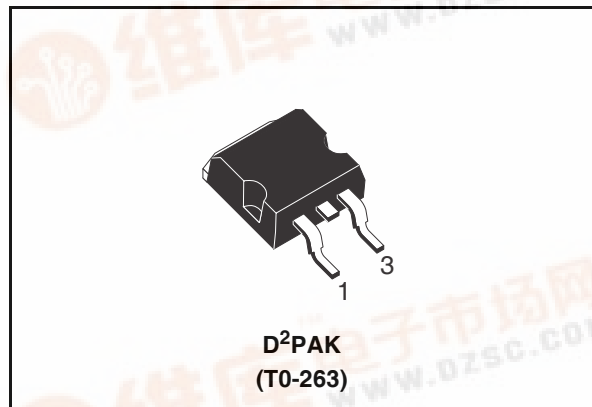
Description

The device is manufactured using high voltage Multi-Epitaxial Planar technology for high switching speeds and medium voltage capability.

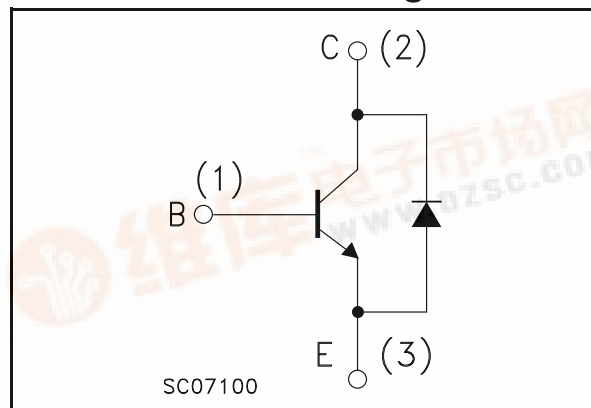
It uses a Cellular Emitter structure to enhance switching speeds.

Applications

- Electronic transformers for halogen lamps
- Switch mode power supplies



Internal schematic diagram



Order codes

Part Number	Marking	Package	Packing
STB13007DT4	B13007D	D²PAK	Tape & Reel

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1 Electrical ratings

Table 1. Absolute maximum rating

Symbol	Parameter	Value	Unit
V_{CEV}	Collector-emitter voltage ($V_{BE} = -1.5V$)	700	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	400	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	9	V
I_C	Collector current	8	A
I_{CM}	Collector peak current ($t_P < 5ms$)	16	A
I_B	Base current	4	A
I_{BM}	Base peak current ($t_P < 5ms$)	8	A
P_{tot}	Total dissipation at $T_c = 25^\circ C$	80	W
T_{stg}	Storage temperature	-65 to 150	$^\circ C$
T_J	Max. operating junction temperature	150	$^\circ C$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.56	$^\circ C/W$
$R_{thj-amb}$	Thermal resistance junction-amb max	62.5	$^\circ C/W$

2 Electrical characteristics

($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise specified)

Table 3. Electrical characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector cut-off current ($V_{\text{BE}} = 0\text{V}$)	$V_{\text{CE}} = 700\text{V}$ $V_{\text{CE}} = 700\text{V}$ $T_{\text{c}} = 100^{\circ}\text{C}$			10 0.5	μA mA
I_{CEO}	Collector cut-off current ($I_{\text{B}} = 0$)	$V_{\text{CE}} = 400\text{V}$			100	μA
I_{EBO}	Emitter cut-off current ($I_{\text{C}} = 0$)	$V_{\text{EB}} = 9\text{V}$			100	μA
$V_{\text{CEO(sus)}}^{(1)}$	Collector-emitter sustaining voltage ($I_{\text{B}} = 0$)	$I_{\text{C}} = 10\text{mA}$	400			V
$V_{\text{CE(sat)}}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 2\text{A}$ $I_{\text{B}} = 0.4\text{A}$ $I_{\text{C}} = 5\text{A}$ $I_{\text{B}} = 1\text{A}$ $I_{\text{C}} = 8\text{A}$ $I_{\text{B}} = 2\text{A}$ $I_{\text{C}} = 5\text{A}$ $I_{\text{B}} = 1\text{A}$ $T_{\text{c}} = 100^{\circ}\text{C}$			0.8 1.5 2 3	V V V V
$V_{\text{BE(sat)}}^{(1)}$	Base-emitter saturation voltage	$I_{\text{C}} = 2\text{A}$ $I_{\text{B}} = 0.4\text{A}$ $I_{\text{C}} = 5\text{A}$ $I_{\text{B}} = 1\text{A}$ $I_{\text{C}} = 5\text{A}$ $I_{\text{B}} = 1\text{A}$ $T_{\text{c}} = 100^{\circ}\text{C}$			1.2 1.6 1.5	V V V
h_{FE}	DC current gain	$I_{\text{C}} = 2\text{A}$ $V_{\text{CE}} = 5\text{V}$ $I_{\text{C}} = 5\text{A}$ $V_{\text{CE}} = 5\text{V}$	18 8		40 25	
V_{f}	Diode forward voltage	$I_{\text{C}} = 3\text{A}$			2.5	V
t_{s} t_{f}	Inductive load Storage time Fall time	$I_{\text{C}} = 5\text{A}$ $V_{\text{Clamp}} = 250\text{V}$ $I_{\text{B1}} = 1\text{A}$ $V_{\text{BE(off)}} = -5\text{V}$ $R_{\text{BB}} = 0\Omega$ $L = 200\mu\text{H}$ (see fig. 11)		1.7 90	2.3 150	μs ns
t_{s} t_{f}	Inductive load Storage time Fall time	$I_{\text{C}} = 5\text{A}$ $V_{\text{Clamp}} = 250\text{V}$ $I_{\text{B1}} = 1\text{A}$ $V_{\text{BE(off)}} = -5\text{V}$ $R_{\text{BB}} = 0\Omega$ $L = 200\mu\text{H}$ $T_{\text{c}} = 125^{\circ}\text{C}$ (see fig. 11)		2.2 150		μs ns

Note (1) Pulsed duration = 300 μs , duty cycle $\leq 1.5\%$

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

Figure 2. Derating curve

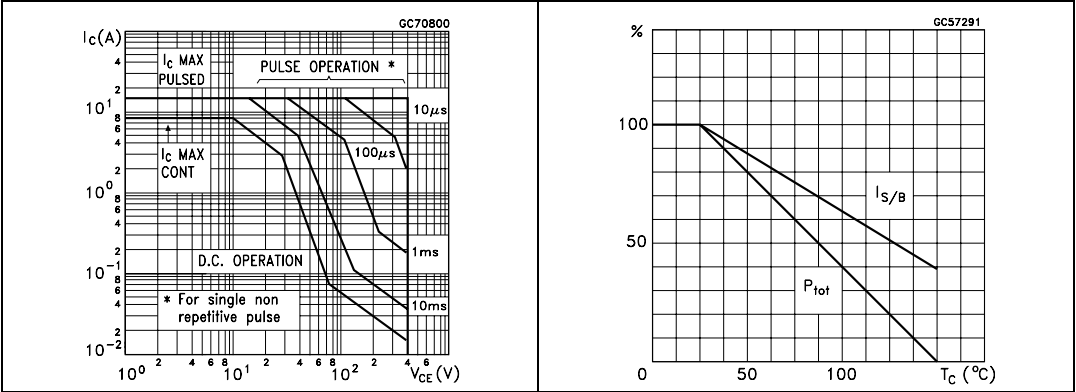


Figure 3. DC current gain

Figure 4. DC current gain

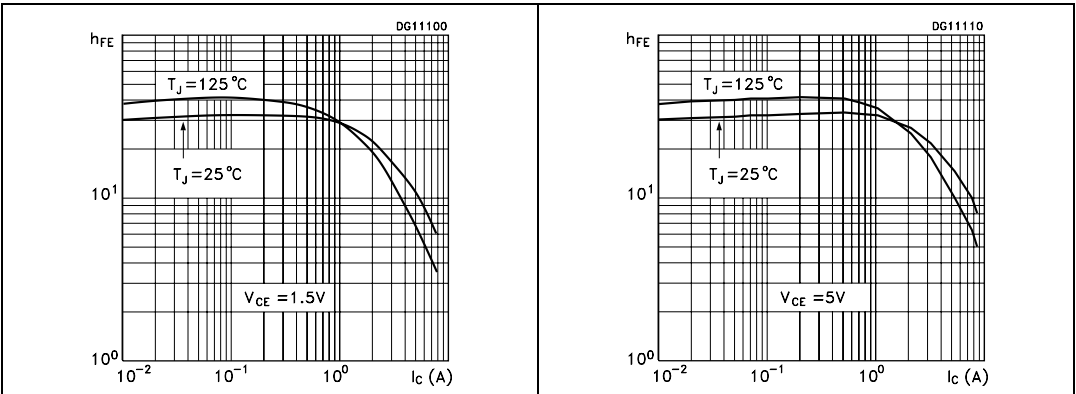


Figure 5. Collector-emitter saturation voltage

Figure 6. Base-emitter saturation voltage

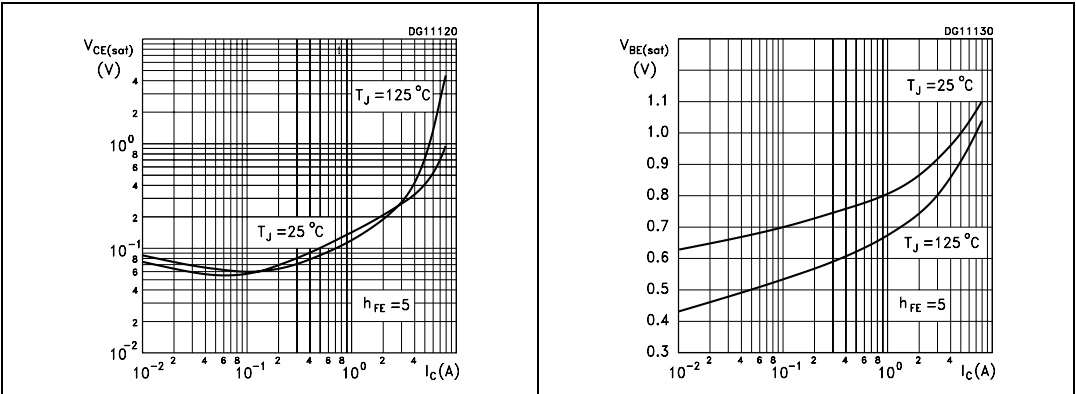


Figure 7. Diode forward voltage

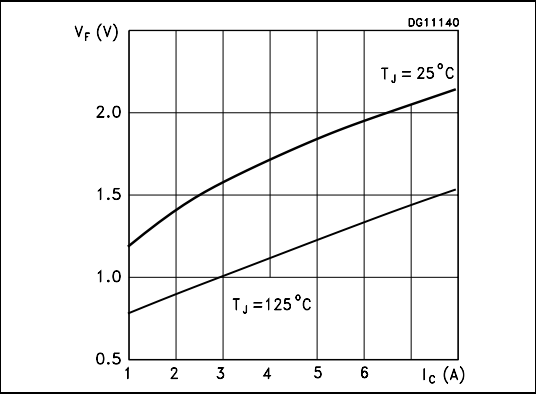


Figure 8. Switching times inductive load

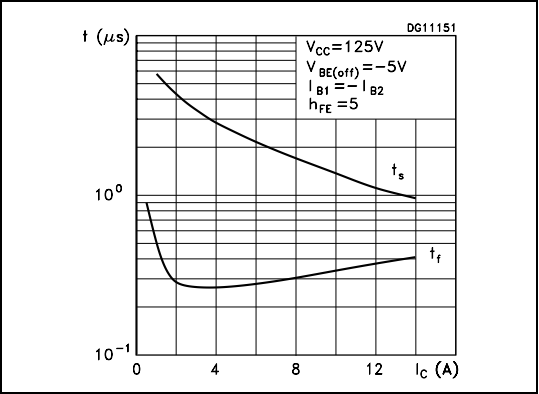


Figure 9. Switching times inductive load

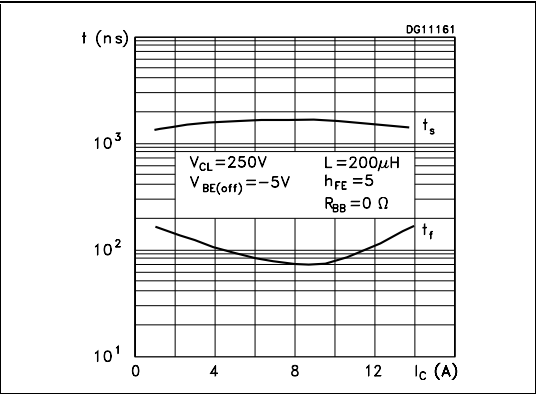
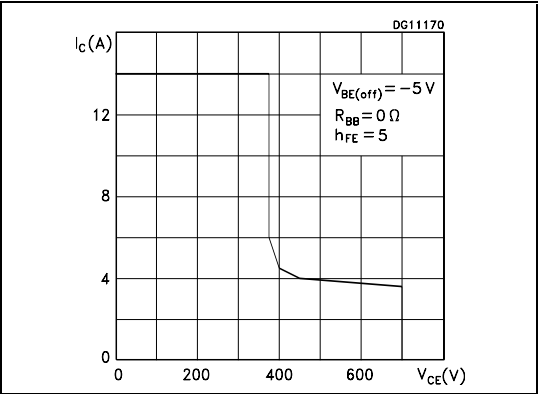
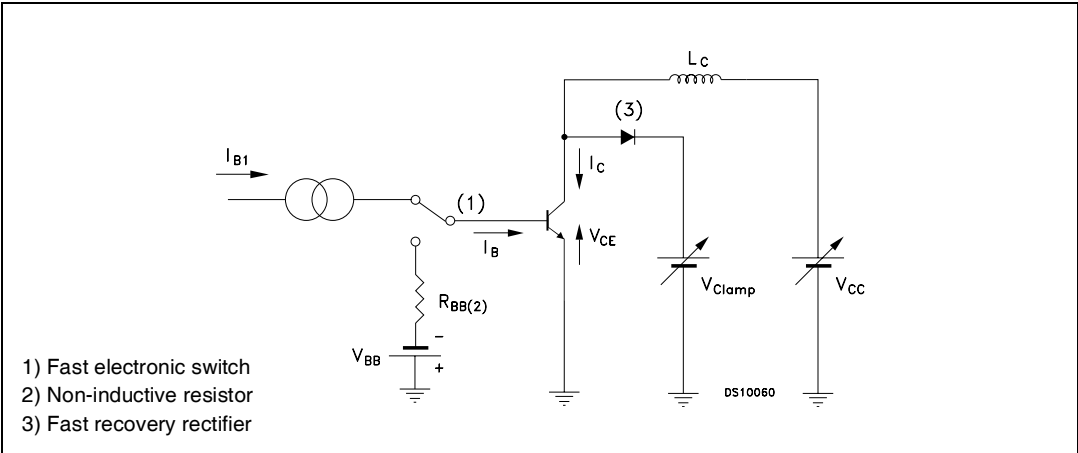


Figure 10. Reverse biased safe operating area



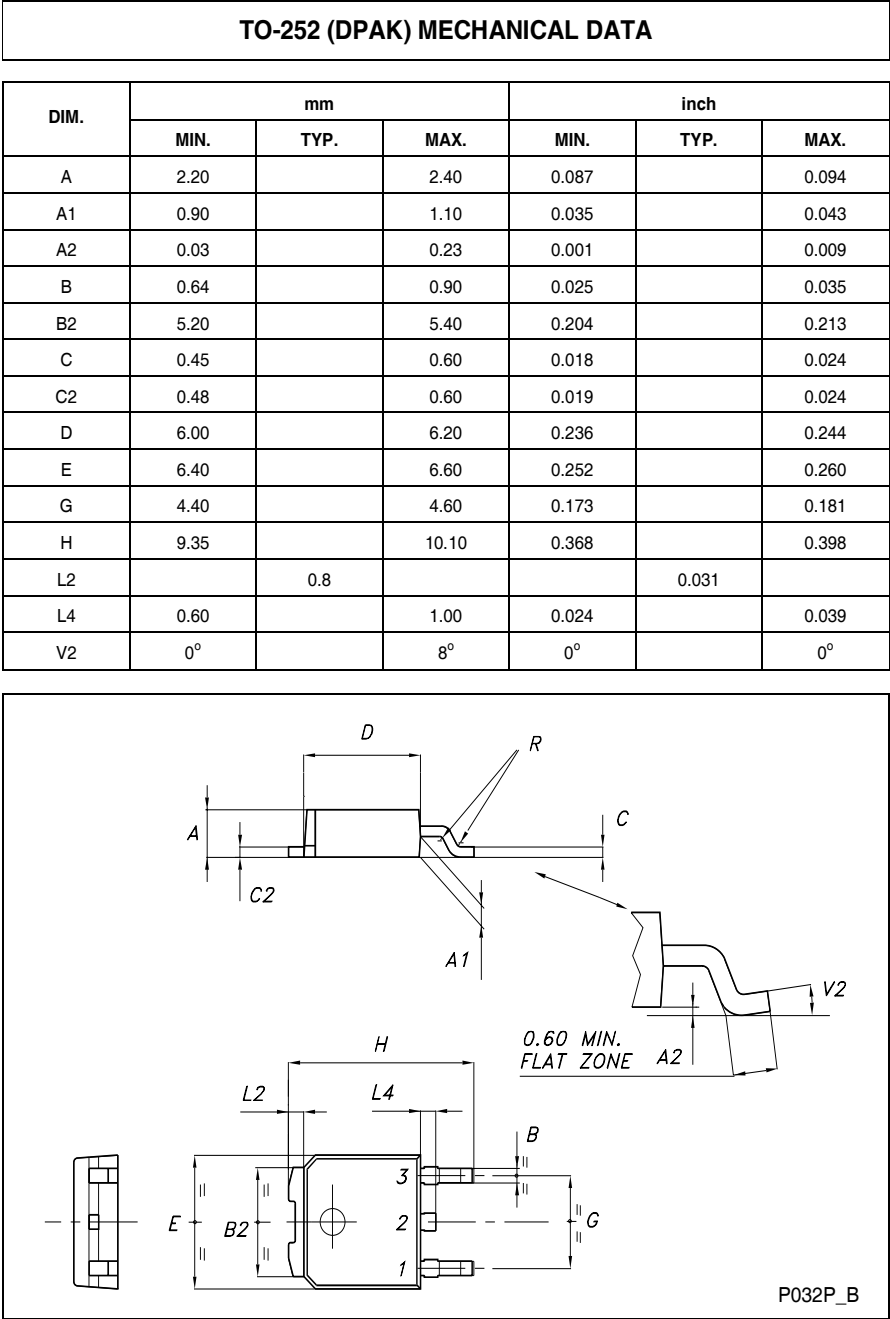
2.2 Test circuits

Figure 11. Inductive load switching test circuit



3 **Package mechanical data**

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



4 Revision history

Table 4. Revision history

Date	Revision	Changes
19-Jun-2006	1	Initial release.

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